KHB9D0N90N1

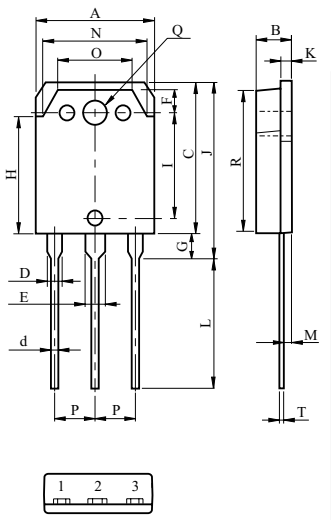
N CHANNEL MOS FIELD EFFECT TRANSISTOR

General Description

This planar stripe MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for electronic ballast and switching mode power supplies.

FEATURES

- $V_{DSS(Min.)}$= 900V, I_D= 9A
- Drain-Source ON Resistance : $R_{DS(ON)}$=1.4 Ω @V_{GS} =10V
- Qg(typ.) =75nC

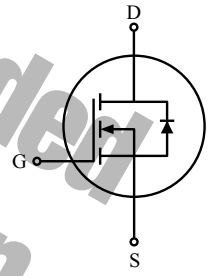


DIM	MILLIMETERS
A	15.60 ± 0.20
B	4.80 ± 0.20
C	19.90 ± 0.20
D	2.00 ± 0.20
d	1.00 ± 0.20
E	3.00 ± 0.20
F	3.80 ± 0.20
G	3.50 ± 0.20
H	13.90 ± 0.20
I	12.76 ± 0.20
J	23.40 ± 0.20
K	1.5+0.15-0.05
L	16.50 ± 0.30
M	1.40 ± 0.20
N	13.60 ± 0.20
O	9.60 ± 0.20
P	5.45 ± 0.30
Q	ϕ 3.20 ± 0.10
R	18.70 ± 0.20
T	0.60+0.15-0.05

TO-3P(N)-E

MAXIMUM RATING (Tc=25℃)

CHARACTERISTIC		SYMBOL	KHB9D0N90N1	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	@T_C=25℃	I_D	9.0	A
	Pulsed (Note1)	I_{DP}	36	
Single Pulsed Avalanche Energy (Note 2)		E_{AS}	900	mJ
Repetitive Avalanche Energy (Note 1)		E_{AR}	20.5	mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.5	V/ns
Drain Power Dissipation	Tc=25℃	P_D	280	W
	Derate above25℃		2.22	W/℃
Maximum Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 150	℃
Thermal Characteristics				
Thermal Resistance, Junction-to-Case		R_{thJC}	0.45	℃/W
Thermal Resistance, Case-to-Sink		R_{thCS}	0.24	℃/W
Thermal Resistance, Junction-to-Ambient		R_{thJA}	40	℃/W



ELECTRICAL CHARACTERISTICS (Tc=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250 μA, V_{GS}=0V	900	-	-	V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_j$	I_D=250 μA, Referenced to 25℃	-	0.99	-	V/℃
Drain Cut-off Current	I_{DSS}	V_{DS}=900V, V_{GS}=0V,	-	-	10	μA
Gate Threshold Voltage	V_{th}	V_{DS}=V_{GS}, I_D=250 μA	2.0	-	4.0	V
Gate Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V	-	-	±100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=4.5A	-	1.12	1.4	Ω
Dynamic						
Total Gate Charge	Q_g	V_{DS}=720V, I_D=9.0A V_{GS}=10V (Note4,5)	-	75	90	nC
Gate-Source Charge	Q_{gs}		-	12	-	
Gate-Drain Charge	Q_{gd}		-	3.5	-	
Turn-on Delay time	$t_{d(on)}$	V_{DD}=450V, R_G=25Ω, I_D=9.0A (Note4,5)	-	48	106	ns
Turn-on Rise time	t_r		-	70	150	
Turn-off Delay time	$t_{d(off)}$		-	289	588	
Turn-off Fall time	t_f		-	117	244	
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	-	2663	3462	pF
Output Capacitance	C_{oss}		-	183	238	
Reverse Transfer Capacitance	C_{rss}		-	20	26	
Source-Drain Diode Ratings						
Continuous Source Current	I_S	V_{GS}<V_{th}	-	-	9.0	A
Pulsed Source Current	I_{SP}		-	-	36.0	
Diode Forward Voltage	V_{SD}	I_S=8.0A, V_{GS}=0V	-	-	1.4	V
Reverse Recovery Time	t_{rr}	I_S=9.0A, V_{GS}=0V, dIs/dt=100A/μs	-	550	-	ns
Reverse Recovery Charge	Q_{rr}		-	6.5	-	μC

Note 1) Repetivity rating : Pulse width limited by junction temperature.

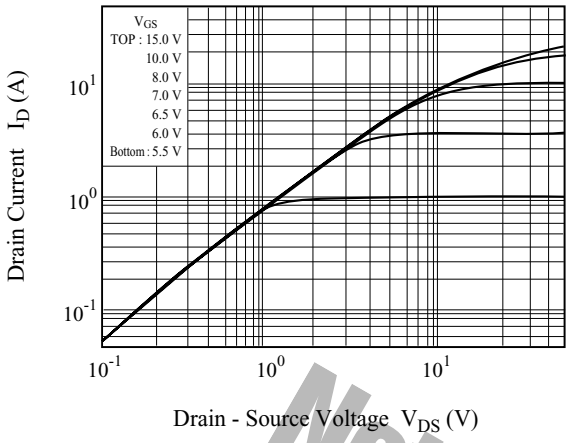
Note 2) L = 21mH, I_{AS}=9.0A, V_{DD}=50V, R_G = 25Ω, Starting T_j = 25℃..0

Note 3) I_S ≤9.0A, dI/dt≤200A/μs, V_{DD}≤BV_{DSS}, Starting T_j = 25℃.

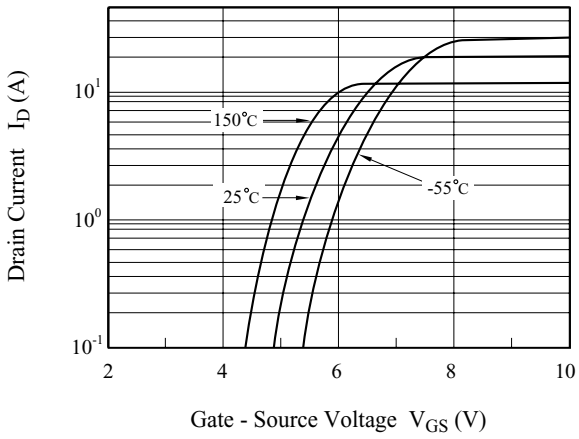
Note 4) Pulse Test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%.

Note 5) Essentially independent of operating temperature.

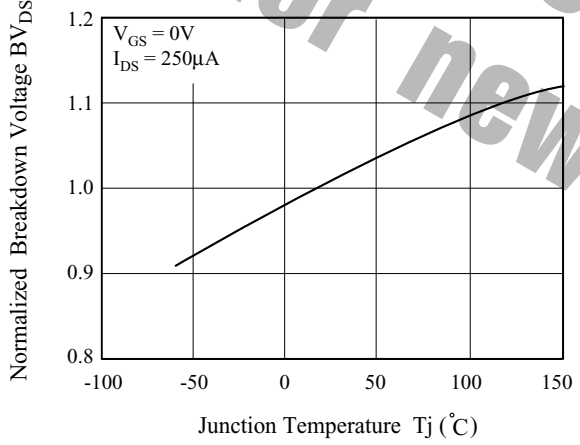
I_D - V_{DS}



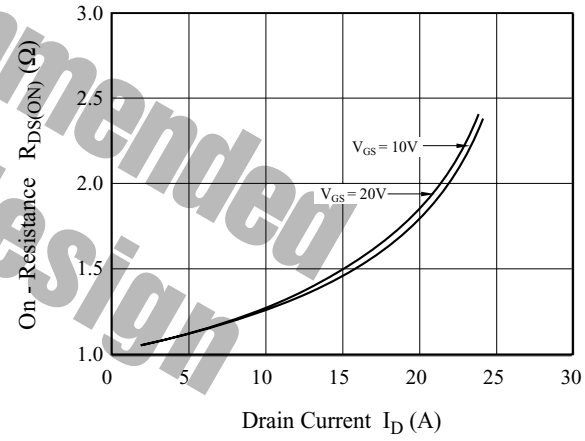
I_D - V_{GS}



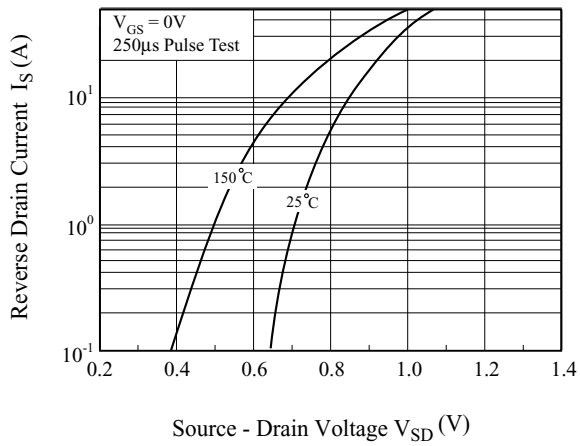
BV_{DSS} - T_j



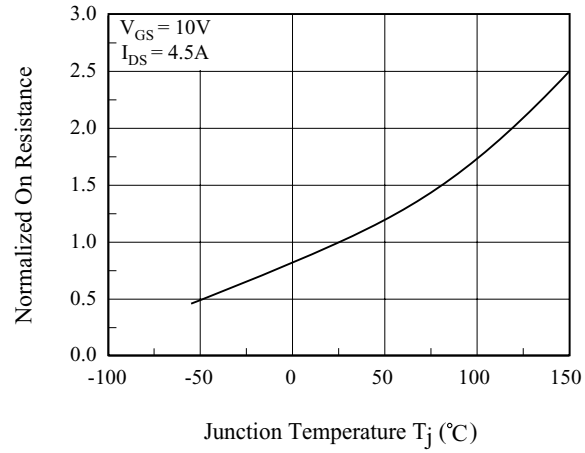
$R_{DS(ON)}$ - I_D



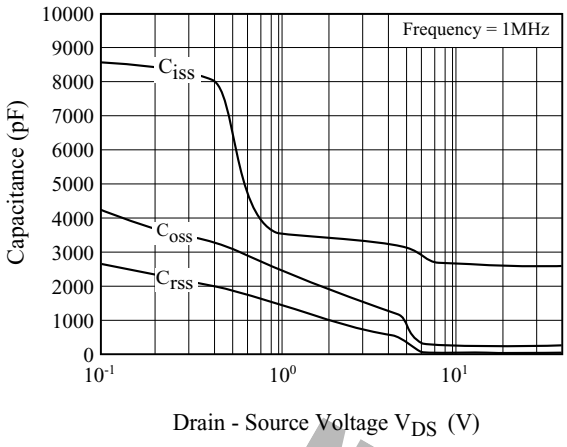
I_S - V_{SD}



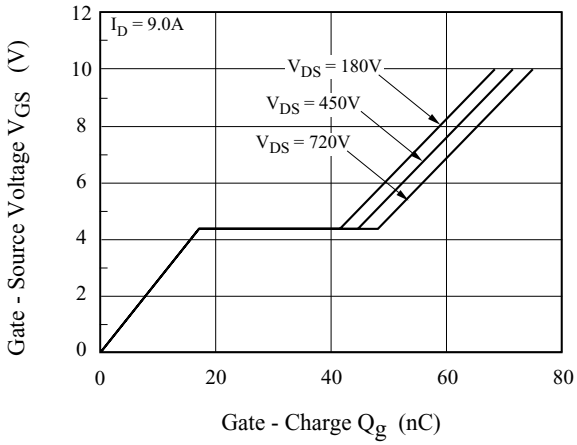
$R_{DS(ON)}$ - T_j



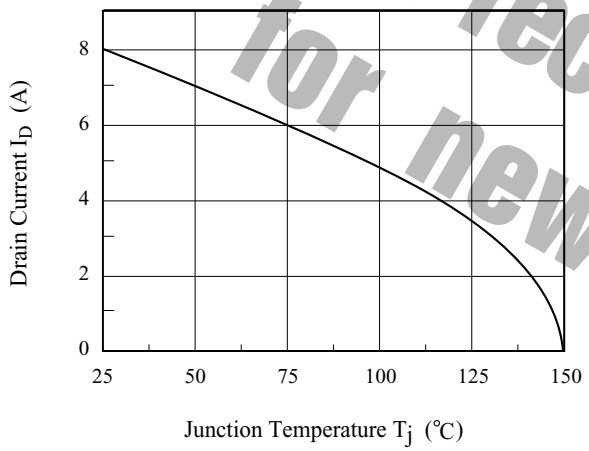
C - V_{DS}



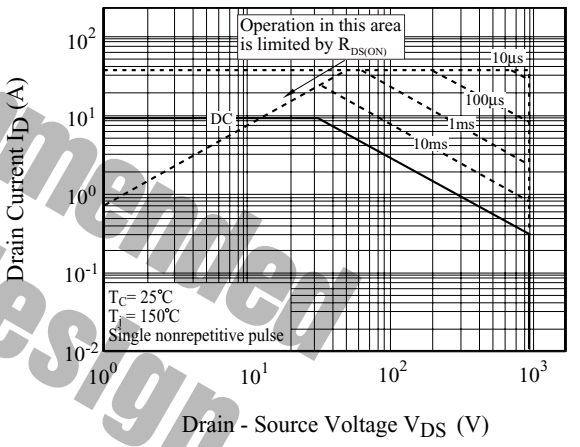
Q_g- V_{GS}



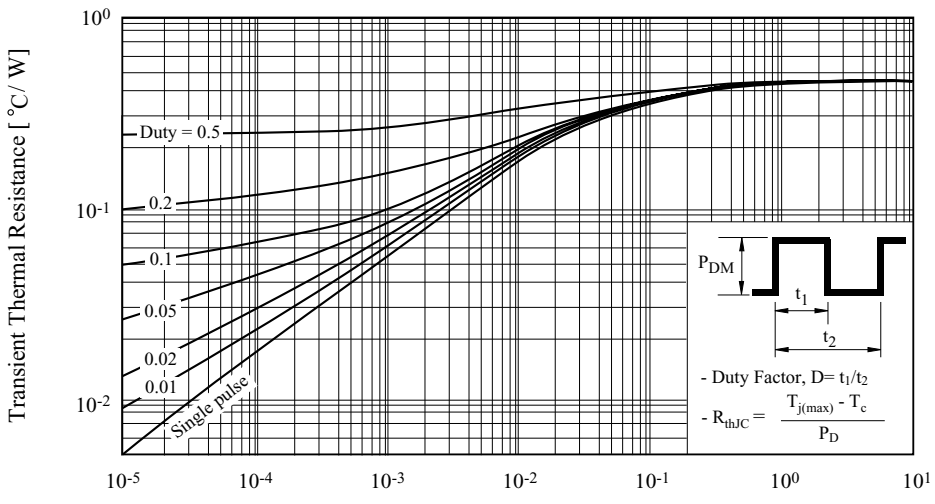
I_D - T_j



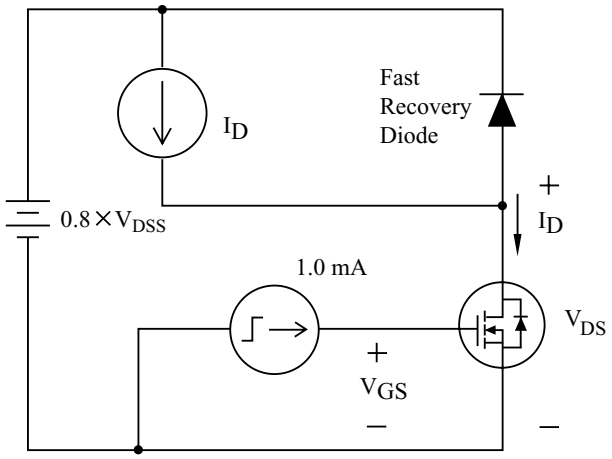
Safe Operation Area

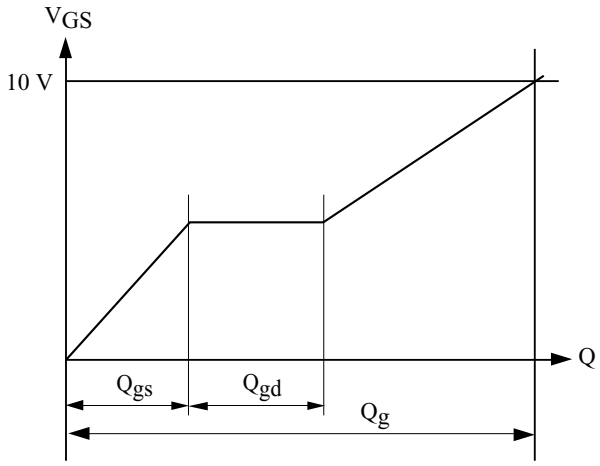


R_{th}

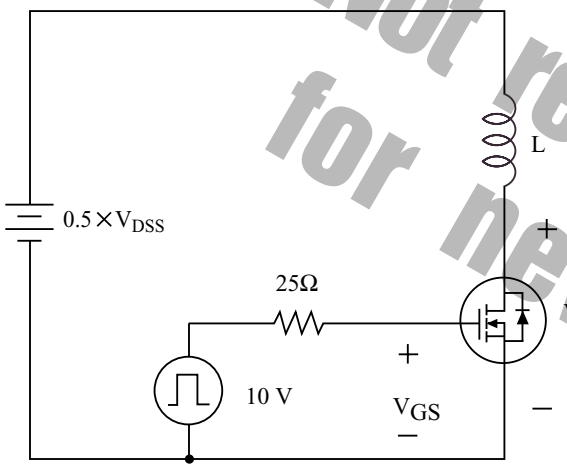


- Gate Charge

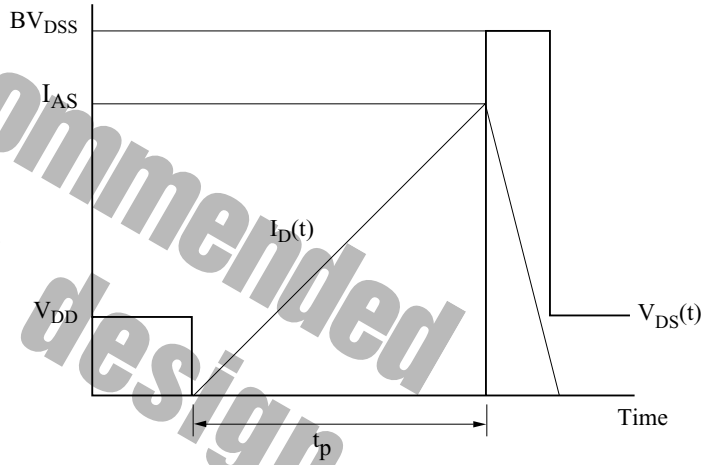




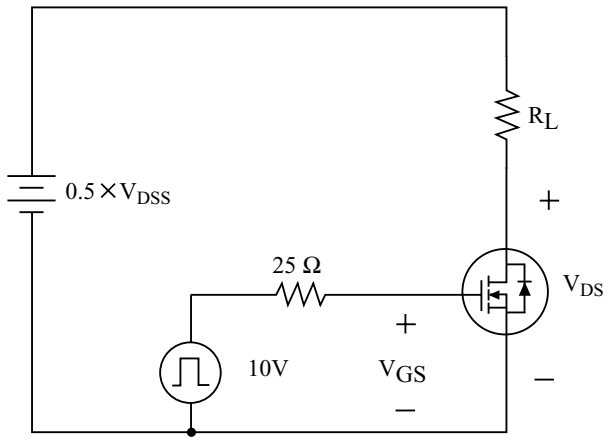
- Single Pulsed Avalanche Energy

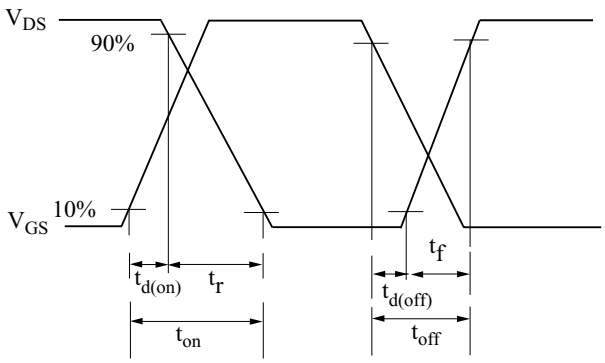


$$E_{AS} = \frac{1}{2} LI_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



- Resistive Load Switching





- Source - Drain Diode Reverse Recovery and dv /dt